

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,012,010 B2
APPLICATION NO. : 10/688439
DATED : March 14, 2006
INVENTOR(S) : Trung Tri Doan et al.

Page 1 of 3

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Col. 5, line 21 –

Replace “O₃ and 88% O₂, at 4000 sccm and helium at from 014 200”

With -- O₃ and 88% O₂, at 4000 sccm and helium at from 0-200--

Col. 8, line 18, claim 5 –

Replace “powers an aspect ratio of the trench from what is was prior”

With --lowers an aspect ratio of the trench from what it was prior--

Col. 8, line, 12

Please insert the following claims:

--6. The method of claim 1 comprising solidifying material of the initially liquid deposition prior to the subsequent initially solid deposition.

7. The method of claim 1 wherein the initially liquid deposition and the initially solid deposition occur at different temperatures.

8. The method of claim 7 wherein the initially liquid deposition is conducted at temperature lower than that of the initially solid deposition.

9. The method of claim 1 comprising annealing the material of the initially liquid deposition prior to the subsequent initially solid deposition.

10. The method of claim 9 wherein the annealing is effective to solidify the material of the initially liquid deposition prior to the subsequent initially solid deposition.

11. The method of claim 1 wherein the initially liquid deposition comprises introducing SiH₄ and H₂O₂ into a chamber within which the semiconductive substrate is received.

12. The method of claim 1 wherein the initially liquid deposition comprises introducing SiH₄, H₂O₂, and N₂ into a chamber within which the semiconductive substrate is received.

13. The method of claim 1 wherein the initially liquid deposition comprises introducing (CH₃)_zSiH_{4-z} and H₂O₂ into a chamber within which the semiconductive substrate is received, where z is at least 1 and no greater than 4.

14. The method of claim 13 wherein the (CH₃)_zSiH_{4-z} comprises CH₃SiH₃.

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,012,010 B2
APPLICATION NO. : 10/688439
DATED : March 14, 2006
INVENTOR(S) : Trung Tri Doan et al.

Page 2 of 3

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Please insert the following claims (cont'd):

15. The method of claim 1 wherein material of the initially liquid deposition deposits over a base of the isolation trench faster than over sidewalls of the isolation trench.

16. The method of claim 1 wherein material of the initially liquid deposition deposits over a base of the isolation trench thicker than over sidewalls of the isolation trench.

17. The method of claim 1 comprising exposing material of the initially liquid deposition to ultraviolet light prior to the subsequent initially solid deposition.

18. The method of claim 17 comprising exposing material of the initially liquid deposition to a temperature greater than a temperature at which the initially liquid deposition initially occurred prior to said exposing to ultraviolet light.

19. The method of claim 1 comprising exposing material of the initially liquid to an electron beam prior to the subsequent initially solid deposition.

20. The method of claim 19 comprising exposing material of the initially liquid deposition to a temperature greater than a temperature at which the initially liquid deposition initially occurred prior to said exposing to the electron beam.

21. The method of claim 1 comprising exposing material of the initially liquid to a plasma prior to the subsequent initially solid deposition.

22. The method of claim 21 comprising exposing material of the initially liquid deposition to a temperature greater than a temperature at which the initially liquid deposition initially occurred prior to said exposing to plasma.

23. The method of claim 1 comprising exposing material of the initially liquid deposition to RF energy prior to the subsequent initially solid deposition.

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,012,010 B2
APPLICATION NO. : 10/688439
DATED : March 14, 2006
INVENTOR(S) : Trung Tri Doan et al.

Page 3 of 3

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Please insert the following claims (cont'd):

24. The method of claim **23** comprising exposing material of the initially liquid deposition to a temperature greater than a temperature at which the initially liquid deposition initially occurred prior to said exposing to RF energy.--

Signed and Sealed this

Seventeenth Day of July, 2007

A handwritten signature in black ink, appearing to read "Jon W. Dudas". The signature is stylized with a large, looped initial "J" and a distinct "D".

JON W. DUDAS
Director of the United States Patent and Trademark Office